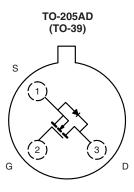
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2N6660, 2N6660-2, 2N6660JANTX, 2N6660JANTXV

Vishay Siliconix

N-Channel 60 V (D-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	60			
$R_{DS(on)} (\Omega)$ at $V_{GS} = 10 V$	3			
Configuration	Single			



Top View

FEATURES

- Military Qualified
- Low On-Resistence: 1.3 Ω
- Low Threshold: 1.7 V
- Low Input Capacitance: 35 pF
- Fast Switching Speed: 8 ns
- Low Input and Output Leakage

BENEFITS

- Guaranteed Reliability
- Low Offset Voltage
- Low-Voltage Operation
- · Easily Driven Without Buffer
- High-Speed Circuits
- Low Error Voltage

APPLICATIONS

- Hi-Rel Systems
- Direct Logic-Level Interface: TTL/CMOS
- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories, Transistors, etc.
- Battery Operated Systems
- Solid-State Relays

ORDERING INFORMATION				
PART	PACKAGE	DESCRIPTION/DSCC PART NUMBER	VISHAY ORDERING PART NUMBER	
2N6660		Commercial	2N6660	
		Commercial, Lead (Pb)-free	2N6660-E3	
2N6660-2	TO-205AD	See -2 Flow Document	2N6660-2	
2N6660JANTX		JANTX2N6660 (std Au leads)	2N6660JTX02	
	(TO-39)	JANTX2N6660 (with solder)	2N6660JTXL02	
		JANTX2N6660P (with PIND)	2N6660JTXP02	
2N6660JANTXV		JANTXV2N6660 (std Au leads)	2N6660JTXV02	
		JANTXV2N6660P (with PIND)	2N6660JTVP02	

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless other	rwise noted)			
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V _{DS}	60	- V	
Gate-Source Voltage		V _{GS}	± 20	v	
Continuous Drain Current (T _{.1} = 150 °C)	T _C = 25 °C	1-	0.99		
Continuous Drain Current $(1j = 150 \text{ C})$	T _C = 100 °C		0.62	А	
Pulsed Drain Current ^a		I _{DM}	3		
Maximum Power Dissipation	T _C = 25 °C	D	6.25	10/	
	T _A = 25 °C		0.725	W	
Thermal Resistance, Junction-to-Ambient ^b		R _{thJA}	170	°C/W	
Thermal Resistance, Junction-to-Case		R _{thJC}	20		
Operating Junction and Storage Temperature R	ange	T _J , T _{stg}	- 55 to 150	°C	

Notes

a. Pulse width limited by maximum junction temperature.

b. Not required by military spec.





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					LIMITS			
PARAMETER	SYMBOL TEST CONDITIONS		ONS	MIN.	TYP. ^a	MAX.	UNIT	
Static								
Drain-Source Breakdown Voltage	V _{DS}	$V_{DS} = 0 V, I_{D} = 10 \mu A$		60	75	-	v	
		$V_{DS} = V_{GS}, I_D = 1 \text{ mA}$		0.8	1.7	2		
Gate-Source Threshold Voltage	V _{GS(th)}			T _C = - 55 °C	-	-	2.5	v
				T _C = 125 °C	0.3	-	-	
Cata Bady Laskaga	$V_{\rm DS} = 0 V$	= 0 V	-	-	± 100			
Gate-Body Leakage	I _{GSS}	$V_{GS} = \pm 20 V$		T _C = 125 °C	-	-	± 500	nA
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} :	= 48 V	-	-	1	
				T _C = 125 °C	-	-	100	μA
On-State Drain Current	I _{D(on)}	$V_{GS} = 10 V$	V _{DS} :	= 10 V	-	2	-	А
		$V_{GS} = 5 V$	I _D = 0.3 A		-	2	5	
Drain-Source On-State Resistance ^b	R _{DS(on)}	V _{GS} = 10 V	I _D :	= 1 A	-	1.3	3	Ω
				T _C = 125 °C	-	2.4	5.6]
Forward Transconductance ^b	g _{fs}	V _{DS} = 7.5 V, I _D = 0.525 A		170	350	-	mS	
Diode Forward Voltage	V _{SD}	I _S = 0.99 A, V _{GS} = 0 V		0.7	0.8	1.6	V	
Dynamic								
Input Capacitance	C _{iss}				-	35	50	
Output Capacitance	Coss	V _{GS} = 0 V V _{DS} = 25 V, f = 1			-	25	40	40 pF 10 -
Reverse Transfer Capacitance	C _{rss}			7, I = 1 IVIHZ	-	7	10	
Drain-Source Capacitance	C _{ds}				-	30	-	
Switching ^c							•	
Turn-On Time	t _{ON}	$V_{DD} = 25 \text{ V}, \text{ R}_{L} = 23 \Omega$ $\text{I}_{D} \cong 1 \text{ A}, \text{ V}_{\text{GEN}} = 10 \text{ V}, \text{ R}_{\text{g}} = 25 \Omega$		-	8	10		
Turn-Off Time	t _{OFF}			-	8.5	10	ns	

Notes

a. FOR DESIGN AID ONLY, not subject to production testing.

b. Pulse test: PW $\leq 300~\mu s$ duty cycle $\leq 2~\%.$

c. Switching time is essentially independent of operating temperature.

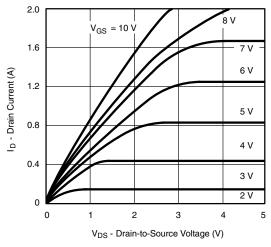
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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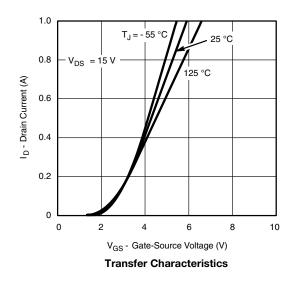
2N6660, 2N6660-2, 2N6660JANTX, 2N6660JANTXV

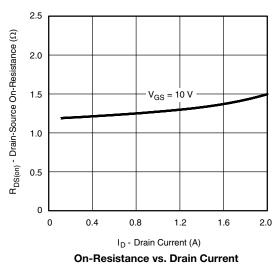
Vishay Siliconix

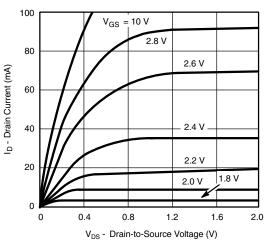
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



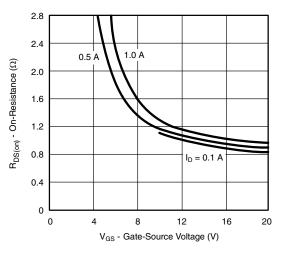
Ohmic Region Characteristics



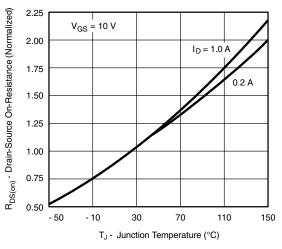




Output Characteristics for Low Gate Drive



On-Resistance vs. Gate-to-Source Voltage



Normalized On-Resistance vs. Junction Temperature

S11-1542-Rev. D, 01-Aug-11

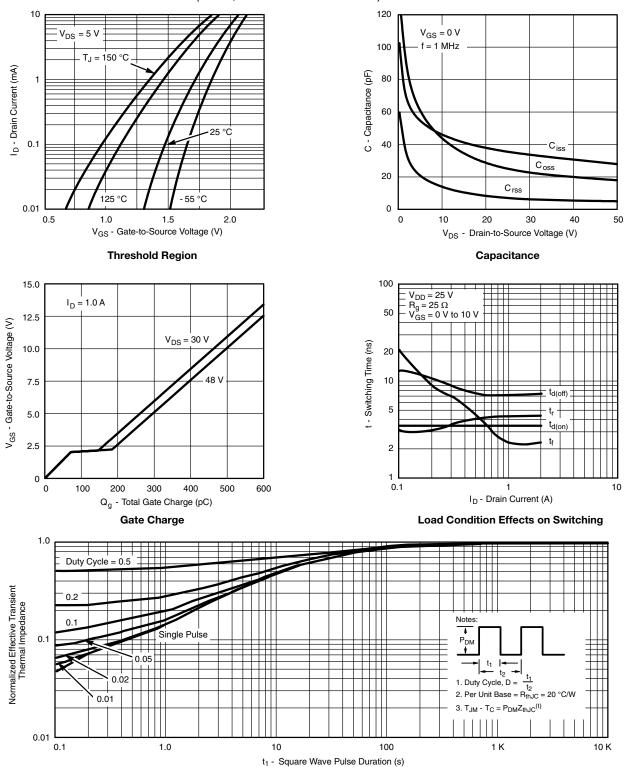
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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?70223.

S11-1542-Rev. D, 01-Aug-11

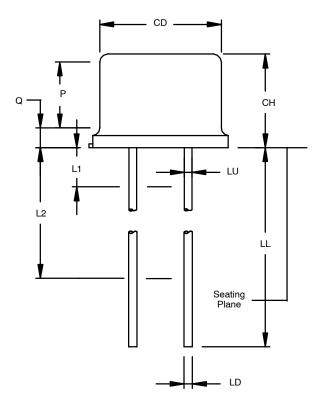
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Document Number: 70223

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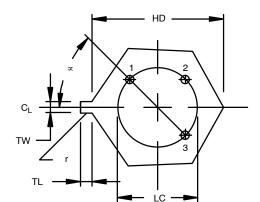
TO-205AD (TO-39 TALL LID)



				IETERS		
Dim	Min	Max	Min	Max	Notes	
CD	0.305	0.335	7.75	8.51		
СН	0.240	0.260	6.10	6.60		
HD	0.335	0.370	8.51	9.40		
LC	0.20	0 TP	5.08	B TP	6	
LD	0.016	0.021	0.41	0.53	7, 8	
LL	0.500	0.750	12.70	19.05	7, 8	
LU	0.016	0.019	0.41	0.48	7, 8	
L1	_	0.050	—	1.27	7, 8	
L2	0.250	_	6.35	—	7, 8	
Ρ	0.100	_	2.54	—	5	
Q	—	0.050	—	1.27	4	
r	_	0.010	_	0.25	9	
TL	0.029	0.045	0.74	1.14	3	
TW	0.028	0.034	0.71	0.86	2	
x	45°	ТР	45° TP		6	
Dimensions	s (see notes	s 1, 2, 9, 11,	12)			

NOTES:

- 1. Dimensions are in inches. Metric equivalents are given for general information only.
- 2. Beyond radius (r) maximum, TW shall be held for a minimum length of 0.011 (0.028 mm).
- 3. Dimension TL measured from maximum HD.
- 4. Outline in this zone is not controlled.
- 5. Dimension CD shall not vary more than 0.010 (0.25 mm) in zone P. This zone is controlled for automatic handling.
- Leads at guage plane 0.054+0.001, -0.000 (1.37+0.03, -0.00 mm) below seating plane shall be within 0.007 (0.18 mm) radius of true position (TP) at maximum material condition (MMC) relative to tab at MMC.
- 7. LU applies between L1 and L2, LD applies between L2 and L maximum. Diameter is uncontrolled in L1 and beyond LL minimum.
- 8. All three leads.
- 9. Radius (r) applies to both inside corners of tab.
- 10. Drain is electrically connected to the case.





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